active component and 7.2 to 49.4 wt.% of nickel oxide, said catalyst containing a composite oxide of aluminum and nickel;

adding steam or a reaction gas containing steam and oxygen to the gas stream; and

effecting a hydrolysis reaction between the at least one compound and the steam, thereby producing a treated gas containing hydrogen fluoride.

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44. (Amended) A process according to Claim 40, wherein the catalyst further comprises 15.1 to 40.6% by weight of zinc oxide.

45. (Amended) A process according to Claim 40, wherein the catalyst consists essentially of alumina and nickel oxide and a composite oxide of aluminum and nickel.

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48. (Amended) A method of treating a gas containing a perfluoro-compound, comprising:

contacting the gas at a temperature of 400 to 800°C with a catalyst comprising aluminum oxide as an active component and 7.2 to 49.4 wt.% of nickel oxide, said catalyst containing a composite oxide of aluminum and nickel, in the presence of steam, whereby the perfluoro-compound is decomposed by hydrolysis to produce a treated gas containing hydrogen fluoride and acidic compounds; and

contacting the treated gas with water to absorb the hydrogen fluoride and the acidic compounds from the treated gas.

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51. (Amended) A process according to Claim 48, wherein the catalyst consists essentially of alumina and nickel oxide and composite oxide of aluminum and nickel.

Please add claims 75-79 as follows:

75. (New) A process according to claim 40, wherein the compound in the gas stream is SF_6.

76. (New) A process according to claim 40, wherein the compound in the gas stream is carbon, fluorine and hydrogen.

77. (New) A process according to claim 40, wherein the compound in the gas stream is NF_3.

78. (New) A process according to claim 40, wherein the compound in the gas stream is at least one member selected from the group consisting of CHF_3, CH_2F_2, CH_3F, C_2HF_5, $C_2H_2F_4$, $C_2H_3F_3$, $C_2H_4F_2$, C_2H_5F, CH_2OCF_2, SF_6 and NF_3.

79. (New) A process according to claim 40, wherein the fluorine compound-containing gas to be treated is used as etchants or cleaners for semiconductors.